

SOT-523 Bias Resistor Transistor NPN Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

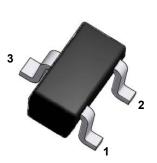
This new series of digital transistors is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors: a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The device is designed for low power surface mount applications.

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage	50	V	
V _{CEO}	Collector-Emitter Voltage	50	V	
Ic	Collector Current	100	mA	
P _D	Power Dissipation	150	mW	
R _{0JA}	Thermal Resistance from Junction to Ambient	600	°C /W	
T _J T _{STG}	Junction & Storage Temperature Range	-55 to +150	°C	

These ratings are limiting values above which the serviceability of the device may be impaired.

Green Product

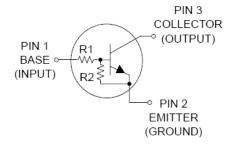


SOT-523 (SC-75A)

Specification Features:

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g

Electrical Symbol:



DB Number: DB-250





Device Marking & Resistor Values:

Device	Marking	R1 (KΩ)	R2 (KΩ)
DTC114EE	24	10	10
DTC124EE	25	22	22
DTC144EE	26	47	47
DTC114YE	64	10	47
DTC114TE	04	10	∞
DTC143TE	03	4.7	∞
DTC123EE	22	2.2	2.2
DTC143EE	23	4.7	4.7
DTC143ZE	E23	4.7	47
DTC124XE	45	22	47
DTC123JE	E42	2.2	47

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Off Characteristics

Symbol	Parameter	Test Condition	Limits			Unit
Symbol	r arailleter	rest condition	Min	Тур	Max	Oilit
I _{CBO}	Collector-Base Cutoff Current	V _{CB} =50V, I _E =0A	-	-	100	nA
I _{CEO}	Collector-Emitter Cutoff Current	V _{CE} =50V, I _B =0A	-	-	500	nA
I _{EBO}	Emitter-Base Cutoff Current	V _{EB} =6.0V, I _C =0A				
	DTC114EE		-	-	0.50	
	DTC124EE		-	-	0.20	
	DTC144EE		-	-	0.10	
	DTC114YE		-	-	0.20	
	DTC114TE		-	-	0.90	mA
	DTC143TE		-	-	1.90	IIIA
	DTC123EE		-	-	2.30	
	DTC143EE		-	-	1.50	
	DTC143ZE		-	-	0.18	
	DTC124XE		-	-	0.13	
	DTC123JE		-	-	0.20	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C =10uA, I _E =0A	50	-	-	Volts
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage (Note 1)	I _C =2.0mAA, I _B =0A	50	-	-	Volts

Note 1: Pulse Test. Pulse width <300us, Duty cycle < 2.0%)

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On Characteristics (Note 1)

Symbol	Parameter	Test Condition	Limits			Unit	
	i arameter		Min	Тур	Max	Oili	
H _{FE}	DC Current Dain	V _{CE} =10V, I _C =5.0mA					
	DTC114EE		35	60	-		
	DTC124EE		60	100	-		
	DTC144EE		80	140	-		
	DTC114YE		80	140	-		
	DTC114TE		160	350	-	m/	
	DTC143TE		160	350	-	mA	
	DTC123EE		8.0	15			
	DTC143EE		15	30			
	DTC143ZE		80	200			
	DTC124XE		80	150			
	DTC123JE		80	140			
$V_{\text{CE(sat)}}$	Collector-Emitter Saturation Voltage						
	DTC114EE	I _C =10mA, I _B =0.3mA					
	DTC124EE	I _C =10mA, I _B =0.3mA			0.25	Volts	
	DTC144EE	I _C =10mA, I _B =0.3mA					
	DTC114YE	I _C =10mA, I _B =0.3mA					
	DTC114TE	I _C =10mA, I _B =1mA					
	DTC143TE	I _C =10mA, I _B =1mA		0.25	VOIT		
	DTC123EE	I _C =10mA, I _D =5mA					
	DTC143EE	I _C =10mA, I _D =1mA					
	DTC143ZE	I _C =10mA, I _D =1mA					
	DTC124XE	I _C =10mA, I _B =1mA					
	DTC123JE	I _C =10mA, I _B =0.3mA					
V _{OL}	Output Voltage (on)	R _L = 1.0KΩ					
	DTC114EE	V _{CC} =5.0V, V _B =2.5V					
	DTC124EE	V _{CC} =5.0V, V _B =2.5V					
	DTC144EE	V _{CC} =5.0V, V _B =3.5V					
	DTC114YE	V _{CC} =5.0V, V _B =2.5V					
	DTC114TE	V _{CC} =5.0V, V _B =2.5V			0.20	Vol	
	DTC143TE	V _{CC} =5.0V, V _B =2.5V			0.20	VOI	
	DTC123EE	V _{CC} =5.0V, V _B =2.5V					
	DTC143EE	V _{CC} =5.0V, V _B =2.5V					
	DTC143ZE	V _{CC} =5.0V, V _B =2.5V					
	DTC124XE	V _{CC} =5.0V, V _B =2.5V					
	DTC123JE	V _{CC} =5.0V, V _B =2.5V					

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On Characteristics

Symbol	Paramet	or	Test Condition		Limits		Unit	
Syllibol	Faramet	GI	rest condition	Min	Тур	Max	Oilit	
V _{OH}	Output Voltage (on)		R _L = 1.0KΩ					
		DTC114EE	V _{CC} =5.0V, V _B =0.5V					
		DTC124EE	V _{CC} =5.0V, V _B =0.5V					
		DTC144EE	V _{CC} =5.0V, V _B =0.5V					
		DTC114YE	V _{CC} =5.0V, V _B =0.5V					
		DTC114TE	V _{CC} =5.0V, V _B =0.25V	4.9			Volts	
		DTC143TE	V _{CC} =5.0V, V _B =0.25V	4.9		4.9		VOIIS
		DTC123EE	V _{CC} =5.0V, V _B =0.5V					
		DTC143EE	V _{CC} =5.0V, V _B =0.5V					
		DTC143ZE	V _{CC} =5.0V, V _B =0.25V					
		DTC124XE	V _{CC} =5.0V, V _B =0.5V					
		DTC123JE	V _{CC} =5.0V, V _B =0.5V					

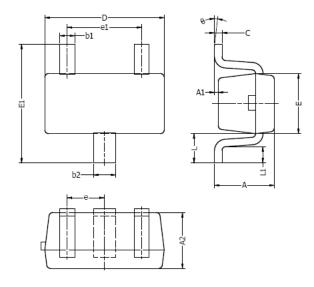
Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Charac	teristic	Min	Тур	Max	Unit
R1	Input Resistor	DTC114EE	7.0	10	13	
		DTC124EE	15.4	22	28.6	
		DTC144EE	32.9	47	61.1	
		DTC114YE	7.0	10	13	
		DTC114TE	7.0	10	13	
		DTC143TE	3.3	4.7	6.1	ΚΩ
		DTC123EE	1.5	2.2	2.9	
		DTC143EE	3.3	4.7	6.1	
		DTC143ZE	3.3	4.7	6.1	
		DTC124XE	15.4	22	28.6	
		DTC123JE	1.54	2.2	2.86	
R1/R2	Resistor Ratio	DTC114EE	0.8	1.0	1.2	
		DTC124EE	0.8	1.0	1.2	
		DTC144EE	0.8	1.0	1.2	
		DTC114YE	0.17	0.21	0.25	
		DTC114TE	-	-	-	
		DTC143TE	-	-	-	
		DTC123EE	0.8	1.0	1.2	
		DTC143EE	0.8	1.0	1.2	
		DTC143ZE	0.055	0.1	0.185	
		DTC124XE	0.38	0.47	0.56	
		DTC123JE	0.038	0.047	0.056	

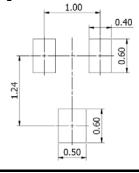
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SOT-523 Package Outline



Typical Soldering Pattern:



DIM	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	0.70	0.90	0.028	0.035	
A1	0.00	0.10	0.000	0.004	
A2	0.70	0.80	0.028	0.031	
b1	0.15	0.25	0.006	0.010	
b2	0.25	0.35	0.010	0.014	
С	0.10	0.20	0.004	0.008	
D	1.50	1.70	0.059	0.067	
E	0.70	0.90	0.028	0.035	
E1	1.45	1.75	0.057	0.069	
е	0.50	TYP.	0.020	TYP.	
e1	0.90	1.10	0.035	0.043	
L	0.40 REF.		0.016	REF.	
L1	0.10	0.30	0.004	0.012	
θ	0 °	8 °	0 °	8 °	

NOTES:

- 1. Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
- 2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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